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cut Particularly, such phenomenon tends to occur at the time of switching on/off the plasma.

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Beginning at page 4, line 8,

A2 Summary of the Invention

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Beginning at page 7, line 2,

A3 (6) Even when the temperature of the base is lowered, the large kinetic energy of the reactive species enables formation of a film of good quality. therefore, the temperature of the base can be further lowered and a large and inexpensive insulating substrate such as a glass substrate or a heat-resistant resin substrate can be used to reduce the cost.

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Beginning at page 10, line 1,

A4 Detailed Description of the Preferred Embodiments

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Beginning at page 25, line 18,

A5 The substrate 1 is heated from the room temperature to 550°C, for example, 200 to 300°C, by the heater wire 51 in the susceptor 45, and the catalyzer 46 is heated for activation to a temperature not higher than the melting point, particularly 800 to 2000°C, as a resistance wire in the hydrogen-based carrier gas, for example, by heating a tungsten wire to approximately 1650°C for activation. The reaction gas 40 is brought in contact with the heated catalyzer 46 of tungsten or the like, and the shutter 47 is opened.

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